



ZHEJIANG UNIÜ-NE Technology CO., LTD

浙江宇力微新能源科技有限公司



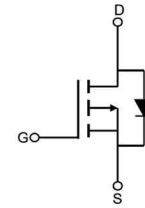
AP40P04K Data Sheet

V 1.1

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Feature

- -40V,-40A
 $R_{DS(ON)} < 13m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 22m\Omega @ V_{GS} = -4.5V$
- Advanced Trench Technology
- Lead free product is acquired
- Excellent $R_{DS(ON)}$ and Low Gate Charge



Schematic Diagram

Application

- PWM applications
- Load Switch
- Power management



Marking and pin assignment

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity (PCS)
40P04K	AP40P04K	TO-252	13 inch	-	2500

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_a = 25^\circ\text{C}$)	I_D	-40	A
Continuous Drain Current ($T_a = 100^\circ\text{C}$)	I_D	-26	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	-160	A
Single Pulsed Avalanche Energy ⁽²⁾	E_{AS}	144	mJ
Power Dissipation	P_D	41.6	W
Thermal Resistance from Junction to Case	$R_{\theta JC}$	3.6	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

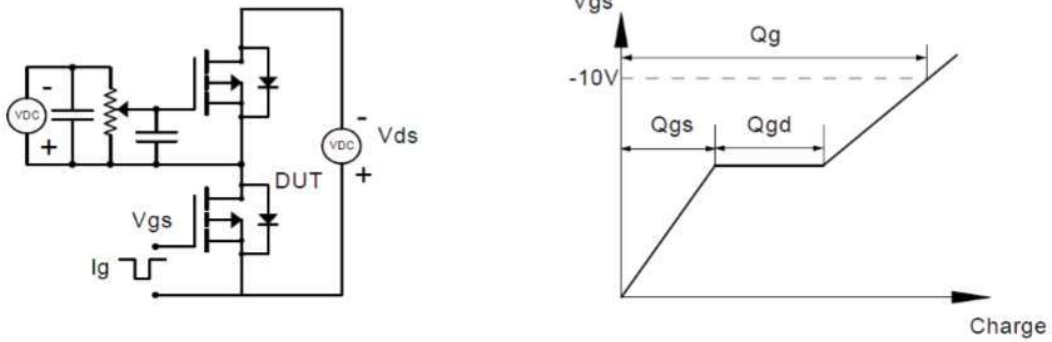
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-40	-	-	V
Zero gate voltage drain current	I _{DSS}	V _{DS} = -40V, V _{GS} = 0V	-	-	1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±100	nA
Gate threshold voltage ⁽³⁾	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1	-1.6	-2.5	V
Drain-source on-resistance ⁽³⁾	R _{DS(on)}	V _{GS} = -10V, I _D = -20A	-	10	13	mΩ
		V _{GS} = -4.5V, I _D = -10A	-	15	22	
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} = -20V, V _{GS} = 0V, f = 1MHz	-	2700	-	pF
Output Capacitance	C _{oss}		-	350	-	
Reverse Transfer Capacitance	C _{rss}		-	265	-	
Switching characteristics						
Turn-on delay time	t _{d(on)}	V _{DD} = -20V, I _D = -20A, R _L = 1Ω V _{GS} = -10V, R _G = 3Ω	-	10	-	ns
Turn-on rise time	t _r		-	21	-	
Turn-off delay time	t _{d(off)}		-	53	-	
Turn-off fall time	t _f		-	29	-	
Total Gate Charge	Q _g	V _{DS} = -20V, I _D = -20A, V _{GS} = -10V	-	42	-	nC
Gate-Source Charge	Q _{gs}		-	7.3	-	
Gate-Drain Charge	Q _{gd}		-	8.5	-	
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V _{DS}	V _{GS} = 0V, I _S = -20A	-	-	-1.2	V
Diode Forward current ⁽⁴⁾	I _S		-	-	-40	A

Notes:

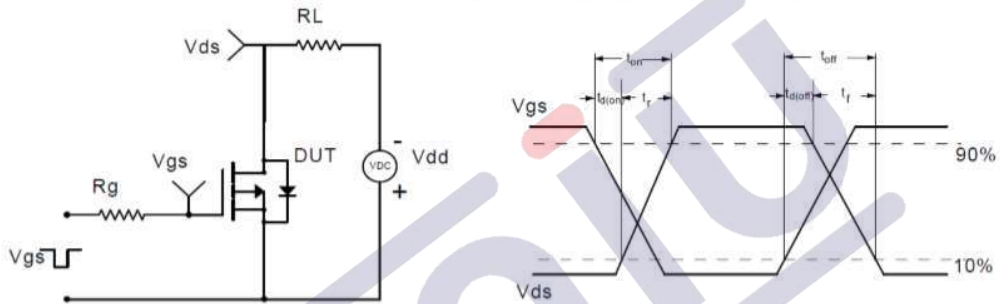
1. Repetitive Rating: pulse width limited by maximum junction temperature
2. EAS Condition: T_J = 25°C, V_{DD} = -20V, R_G = 25 Ω, L = 0.5mH, I_{AS} = -24A
3. Pulse Test: pulse width ≤ 300μs, duty cycle ≤ 2%
4. Surface Mounted on FR4 Board, t ≤ 10 sec

Test Circuit

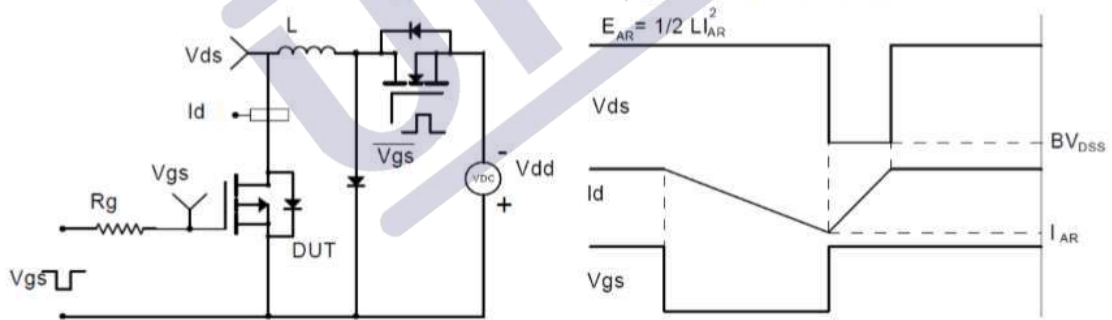
Gate Charge Test Circuit & Waveform



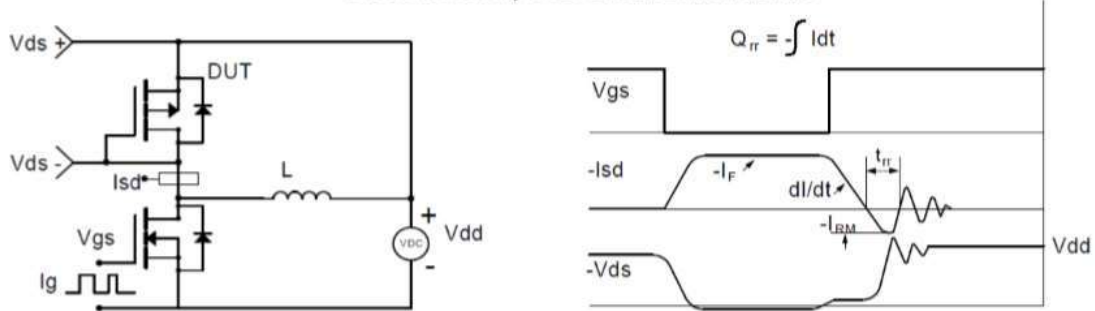
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Typical Performance Characteristics

Figure 1: Output Characteristics

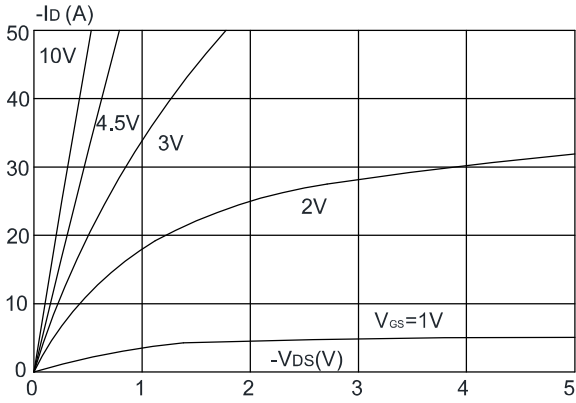


Figure 2: Typical Transfer Characteristics

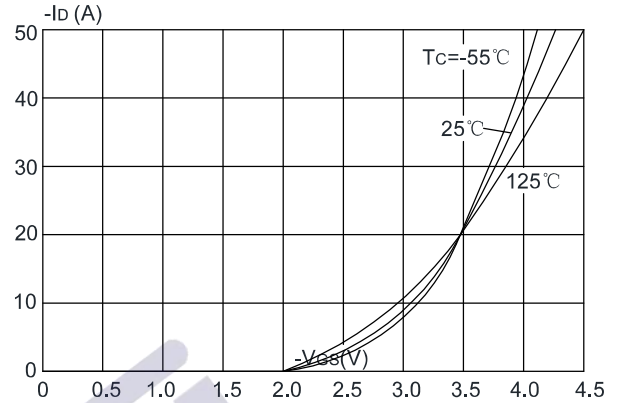


Figure 3: On-resistance vs. Drain Current

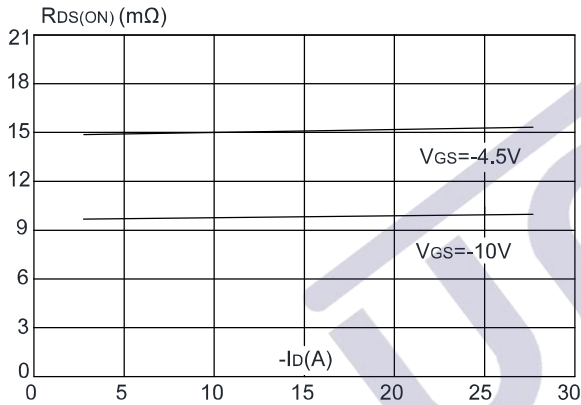


Figure 4: Body Diode Characteristics

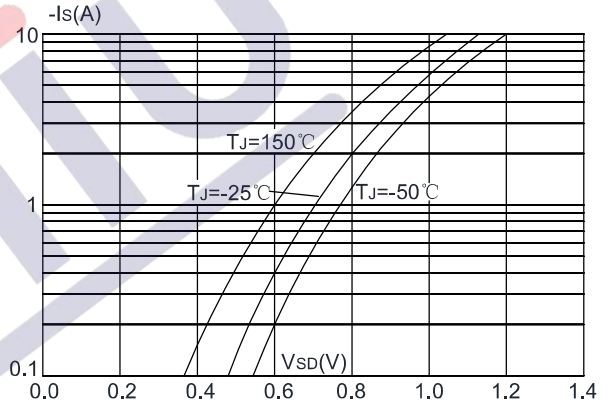


Figure 5: Gate Charge Characteristics

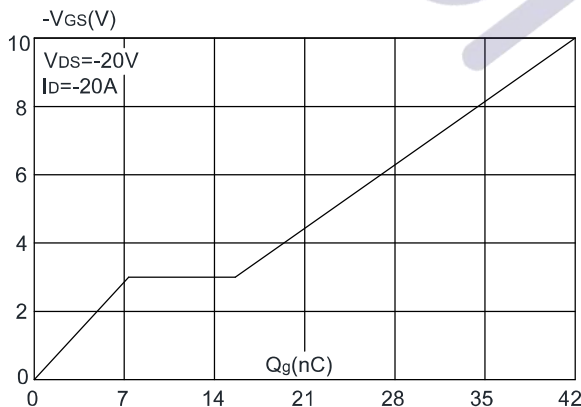


Figure 6: Capacitance Characteristics

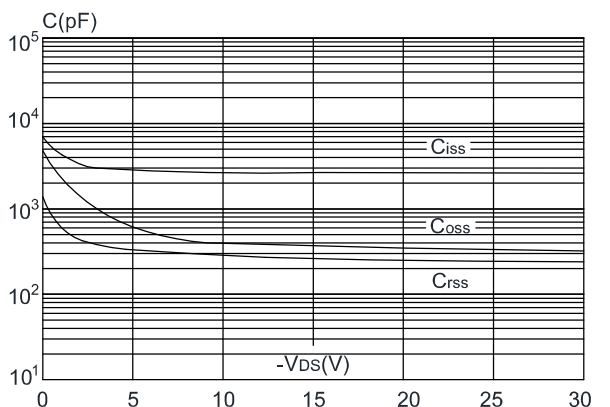


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

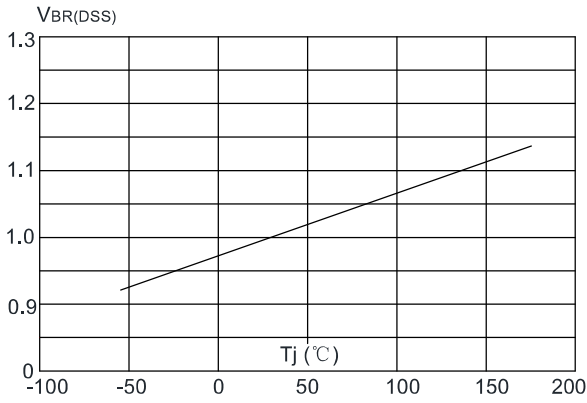


Figure 8: Normalized on Resistance vs. Junction Temperature

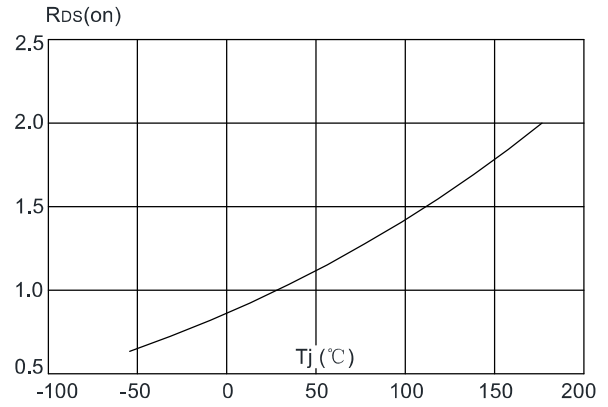


Figure 9: Maximum Safe Operating Area

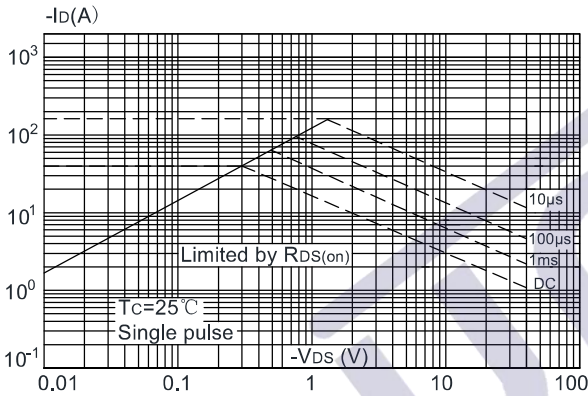


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

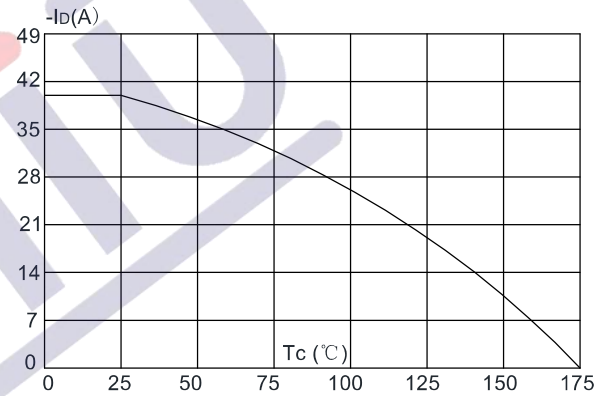
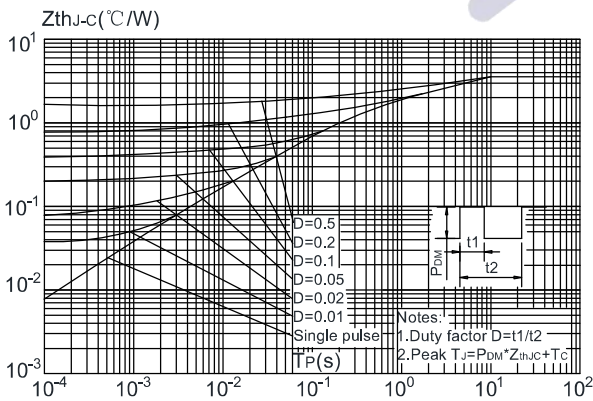
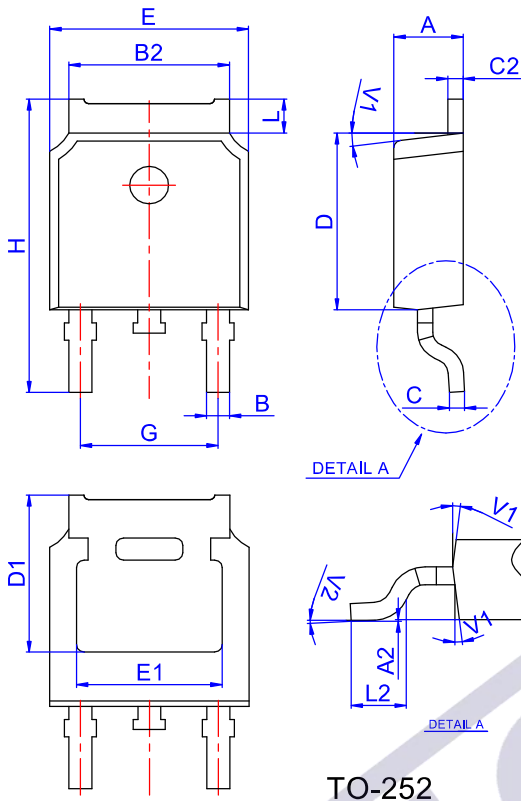


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

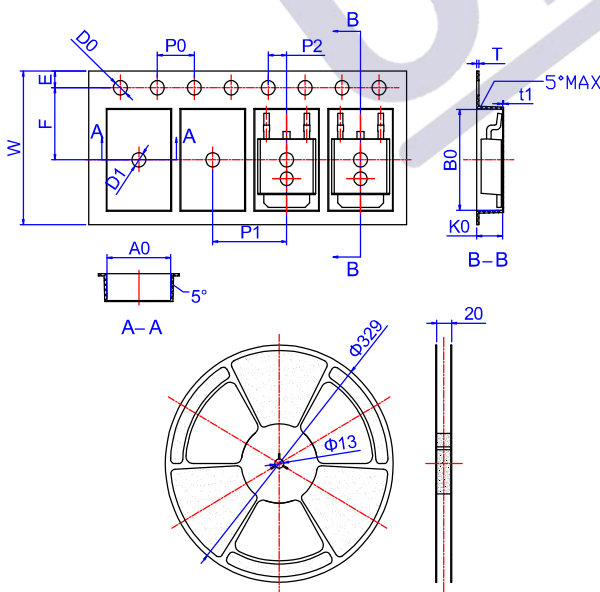


TO-252 Package Information



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

1.版本记录

DATE	REV.	DESCRIPTION
2018/11/15	1.0	First Release
2020/09/18	1.1	Layout adjustment

2.免责声明

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